

Radiation Hardened 8-channel 100MHz Transceiver

with cold sparing

1 GENERAL DESCRIPTION

The AF54RHC245 is a radiation-hardened by design **8-bit 100MHz transceiver with 3-state outputs** that is ideally suited for space, medical imaging and other applications demanding radiation tolerance and high reliability. It is fabricated in a 180 nm CMOS process utilizing proprietary radiation-hardening techniques, delivering high resiliency to single-event effects (SEE) and to a total ionizing dose (TID) to 300 krad (Si).

This device is a member of the Apogee Semiconductor [AF54RHC logic family](#) operating across a voltage supply range of **1.65 V to 5.5 V**.

An output enable control pin allows all buffers to be placed in a high impedance (high-Z) state, simplifying usage in applications with shared busses or mixed power domains. A direction control pin is used to determine whether data flow is A→B or B→A.

Zero-power penalty™ cold-sparing is supported, along with Class 2 ESD protection on all inputs and outputs. A proprietary output stage and robust power-on reset (POR) circuit allow the AF54RHC245 to be cold-spared in any redundant configuration with no static power loss on any pad of the device. The redundant output stage also features a high drive capability with low static power loss.

The AF54RHC245 also features a triple-redundant design throughout its entire circuitry, which allows it to be immune to single-event transients (SET) without requiring additional redundant devices.

Ordering information may be found in [Table 9](#) on [Page 12](#).

1.1 FEATURES

- Proprietary **cold-sparing** capability with zero static power penalty
- **Built-in triple redundancy** for enhanced reliability
- Internal power-on reset (POR) circuitry ensures reliable power up and power down responses during hot plug and cold sparing operations
- Tri-state output drivers
- Class 2 ESD protection (4000 V HBM, 500 V CDM)
- TID resilience of **300 krad (Si)**.
- SEL immune to LET of **80 MeV-cm²/mg**

1.2 LOGIC DIAGRAM

The AF54RHC245 logic function is shown below:

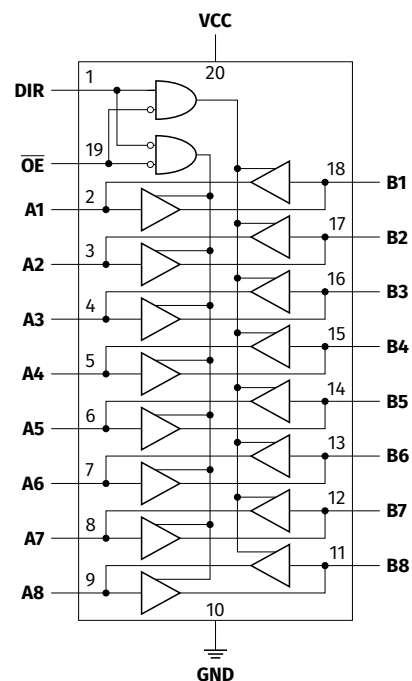


Figure 1: AF54RHC245 logic diagram

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2 ACRONYMS AND ABBREVIATIONS

ESD	Electrostatic Discharge
POR	Power On Reset
RHA	Radiation Hardness Assurance
SEE	Single Event Effects
SEL	Single Event Latchup
SET	Single Event Transient
TID	Total Ionizing Dose
TMR	Triple Modular Redundancy
CDM	Charged-device Model
HBM	Human-body Model

3 LOGIC DATA

The AF54RHC245 truth table is found in Table 1. **H** indicates HIGH logic level, **L** indicates LOW logic level, **X** indicates DON'T CARE and **Z** indicates HIGH-Z (TRI-STATE).

Table 1: AF54RHC245 device truth table

\overline{OE}	DIR	Function
H	X	All buffers tri-state (HIGH-Z)
L	L	A bus to B bus
L	H	B bus to A bus

4 PIN CONFIGURATION

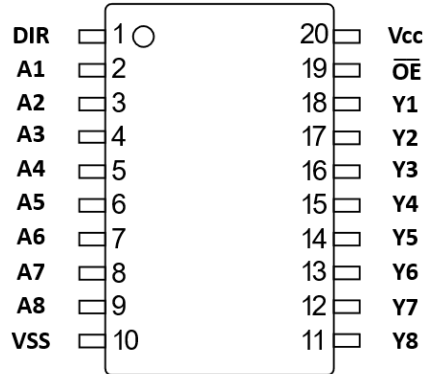


Figure 2: AF54RHC245 device pinout overview

Table 2: AF54RHC245 device pinout description

PIN NAME(S)	PIN NUMBER(S)	DESCRIPTION
A1, A2, A3, A4, A5, A6, A7, A8	2, 3, 4, 5, 6, 7, 8, 9	A Side Inputs (DIR = L) or 3-State Outputs (DIR = H)
B1, B2, B3, B4, B5, B6, B7, B8	18, 17, 16, 15, 14, 13, 12, 11	B Side Inputs (DIR = H) or 3-State Outputs (DIR = L)
DIR	1	Direction Control Input
\overline{OE}	19	Output Enable (active-low)
V _{CC}	20	Positive Voltage Supply
GND	10	Ground

5 ELECTRICAL CHARACTERISTICS

The sign convention for current follows JEDEC standards with negative values representing current sourced from the device and positive values representing current sunk into the device.

5.1 ABSOLUTE MAXIMUM RATINGS

Excursions beyond the values listed in Table 3 may cause permanent damage to the device. Proper function of the device cannot be guaranteed if these values are exceeded, and long-term device reliability may be affected. Functionality of the device at these values, or beyond those listed in [Recommended Operating Conditions](#) (Table 4) is not guaranteed.

All parameters are specified across the entire operating temperature range unless otherwise specified.

Table 3: Absolute Maximum Ratings

SYMBOL	PARAMETER	VALUE	UNITS	
V_{CC}	Supply Voltage	-0.5 to +5.5	V	
V_I	Input voltage range	-0.5 to +5.5	V	
V_O	Output voltage range	-0.5 to $V_{CC} + 0.5$ ⁽¹⁾	V	
$I_{IK} (V_I < 0)$	Input clamp current	100	mA	
I_O	Continuous output current (per pin)	100	mA	
I_{CC}	Maximum supply current	100	mA	
V_{ESD}	ESD Voltage	HBM	4000	V
		CDM	500	V
T_J	Operating junction temperature range	-55 to +150	°C	
T_{STG}	Storage temperature range	-65 to +150	°C	

⁽¹⁾ V_O must remain below absolute maximum rating of V_{CC}

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5.2 RECOMMENDED OPERATING CONDITIONS

All recommended parameters below are specified across the entire operating temperature range unless otherwise specified.

Table 4: Recommended Operating Conditions

SYMBOL	PARAMETER	MIN	MAX	UNITS	
V_{CC}	Supply voltage	1.65	5.5	V	
V_I	Input voltage range	0	5.5	V	
V_O	Output voltage range	0	V_{CC}	V	
V_{IH}	HIGH-level input voltage	$V_{CC} = 1.65$ to 1.95 V	1.4	-	V
		$V_{CC} = 2.3$ to 2.7 V	1.9	-	
		$V_{CC} = 3.0$ to 3.6 V	2.5	-	
		$V_{CC} = 4.5$ to 5.5 V	3.8	-	
V_{IL}	LOW-level input voltage	$V_{CC} = 1.65$ to 1.95 V	-	0.4	V
		$V_{CC} = 2.3$ to 2.7 V	-	0.6	
		$V_{CC} = 3.0$ to 3.6 V	-	0.9	
		$V_{CC} = 4.5$ to 5.5 V	-	1.35	
I_{OH}	HIGH-level output current	$V_{CC} = 1.65$ to 1.95 V	-	-4	mA
		$V_{CC} = 2.3$ to 2.7 V	-	-8	
		$V_{CC} = 3.0$ to 3.6 V	-	-16	
		$V_{CC} = 4.5$ to 5.5 V	-	-24	
I_{OL}	LOW-level output current	$V_{CC} = 1.65$ to 1.95 V	-	4	mA
		$V_{CC} = 2.3$ to 2.7 V	-	8	
		$V_{CC} = 3.0$ to 3.6 V	-	16	
		$V_{CC} = 4.5$ to 5.5 V	-	24	
t_r, t_f	Input rise or fall time (10% - 90%)	$V_{CC} = 1.65$ to 1.95 V	-	1000	ns
		$V_{CC} = 2.3$ to 2.7 V	-	600	
		$V_{CC} = 3.0$ to 3.6 V	-	500	
		$V_{CC} = 4.5$ to 5.5 V	-	400	

Table 5: Thermal Information

SYMBOL	PARAMETER	MIN	TYP	MAX	UNITS
T_J	Operating junction temperature	-55	-	+125	°C
$R_{\theta JA}$	Junction to ambient thermal resistance	-	100	-	°C/W

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5.3 STATIC CHARACTERISTICS

All parameters are specified across the entire operating temperature range unless otherwise specified.

Table 6: DC Electrical Characteristics

SYMBOL	PARAMETER	CONDITIONS	V _{CC}	MIN	TYP	MAX	UNITS
V _{OL}	LOW-level output voltage	I _O = 100 μA	1.65 to 5.5 V	-	TBD	0.05	V
		I _O = 1 mA	1.65 to 5.5 V	-	TBD	0.15	V
		I _O = 4 mA	1.65 V	-	TBD	0.8	V
			2.3 V	-	TBD	0.6	V
			3.0 V	-	TBD	0.4	V
			4.5 V	-	TBD	0.4	V
		I _O = 8 mA	2.3 V	-	TBD	1.0	V
			3.0 V	-	TBD	0.8	V
			4.5 V	-	TBD	0.6	V
		I _O = 16 mA	3.0 V	-	TBD	1.4	V
			4.5 V	-	TBD	1.5	V
		I _O = 24 mA	4.5 V	-	TBD	1.5	V
V _{OH}	HIGH-level output voltage	I _O = -100 μA	1.65 to 5.5 V	V _{CC} - 0.1	V _{CC} - TBD	-	V
		I _O = -1 mA	1.65 to 5.5 V	V _{CC} - 0.15	V _{CC} - TBD	-	V
		I _O = -4 mA	1.65 V	1	TBD	-	V
			2.3 V	1.8	TBD	-	V
			3.0 V	2.6	TBD	-	V
			4.5 V	4.2	TBD	-	V
		I _O = -8 mA	2.3 V	1.4	TBD	-	V
			3.0 V	2.2	TBD	-	V
			4.5 V	3.9	TBD	-	V
		I _O = -16 mA	3.0 V	1.5	TBD	-	V
			4.5 V	3.3	TBD	-	V
		I _O = -24 mA	4.5 V	3.0	TBD	-	V
I _{CC}	Supply current (quiescent)	V _I = V _{CC} or GND, \overline{OE} = GND, I _O = 0 mA	5.5 V	-	166	330	μA
I _I	Input current	V _I = V _{CC} or GND	1.65 to 5.5 V	-	-	±1	μA
I _{OZ}	Output leakage current	V _I = V _{CC} or GND \overline{OE} = V _{CC}	1.65 to 5.5 V	-	-	±5	μA
I _{OFF}	Powerdown leakage current ⁽¹⁾	V _I = 5.5 V or GND	OFF ⁽²⁾	-	-	5	μA

⁽¹⁾ into any input or output port

⁽²⁾ V_{CC} is at GND potential

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5.4 DYNAMIC CHARACTERISTICS

All parameters are specified across the entire operating temperature range unless otherwise specified.

Table 7: AC Electrical Characteristics

SYMBOL	PARAMETER	CONDITIONS	V _{CC}	MIN	TYP	MAX	UNITS
t_{pd} ⁽¹⁾	Propagation delay (Input A to output B or input B to output A)	C _L = 50 pF	4.5 to 5.5 V	-	TBD	TBD	ns
			3.0 to 3.6 V	-	TBD	TBD	ns
			2.3 to 2.7 V	-	TBD	TBD	ns
			1.65 to 1.95 V	-	TBD	TBD	ns
t_{en} ⁽²⁾	Output enable time (Input OE to Output A or B)	C _L = 50 pF	4.5 to 5.5 V	-	TBD	TBD	ns
			3.0 to 3.6 V	-	TBD	TBD	ns
			2.3 to 2.7 V	-	TBD	TBD	ns
			1.65 to 1.95 V	-	TBD	TBD	ns
t_{dis} ⁽³⁾	Output Disable Time (Input OE to Output A or B)	C _L = 50 pF	4.5 to 5.5 V	-	TBD	TBD	ns
			3.0 to 3.6 V	-	TBD	TBD	ns
			2.3 to 2.7 V	-	TBD	TBD	ns
			1.65 to 1.95 V	-	TBD	TBD	ns
t_{sk}	Channel-to-channel skew	C _L = 50 pF	1.65 to 5.5 V	-	-	TBD	ns
C_{in}	Input Capacitance ⁽⁴⁾	V _I = V _{CC} or GND	1.65 to 5.5 V	-	2	4	pF
C_{pd}	Power dissipation capacitance ⁽⁴⁾	I _O = 0 mA, f = 1 MHz	5.5 V	-	40	-	pF

- (1) equivalent to t_{PLH}, t_{PHL}
- (2) equivalent to t_{PZL}, t_{PZH}
- (3) equivalent to t_{PLZ}, t_{PHZ}
- (4) guaranteed by design

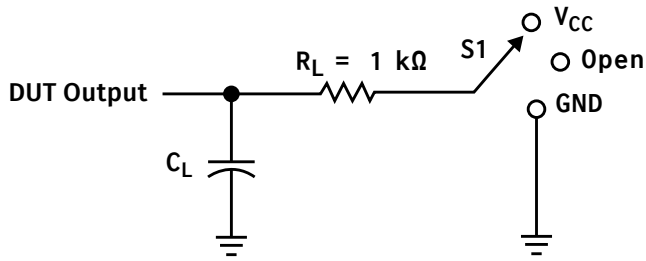
5.5 RADIATION RESILIENCE

For detailed radiation testing reports, please contact Apogee Semiconductor at sales@apogeesemi.com.

Table 8: Radiation Resilience Characteristics

PARAMETER	CONDITIONS	VALUE	UNITS
Total Ionizing Dose (TID)	Please contact Apogee Semiconductor for test report.	300	krad (Si)
SEE Onset LET Threshold	Please contact Apogee Semiconductor for test report.	≥80	MeV-cm ² /mg

5.6 CHARACTERISTICS MEASUREMENT INFORMATION



TEST	S1
t_{pd}	GND
t_{PLZ} , t_{PZL}	V_{CC}
t_{PHZ} , t_{PZH}	GND

Figure 3: Load circuit for 3-state outputs

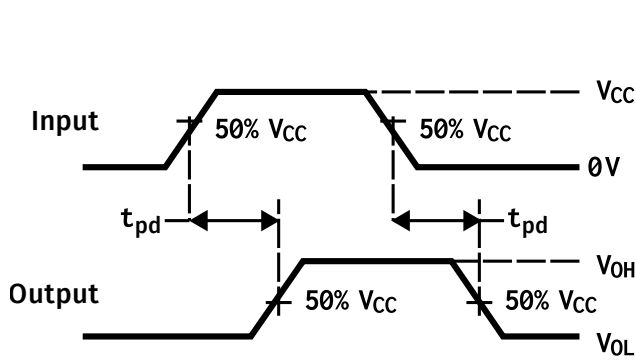


Figure 4: Propagation delay measurement

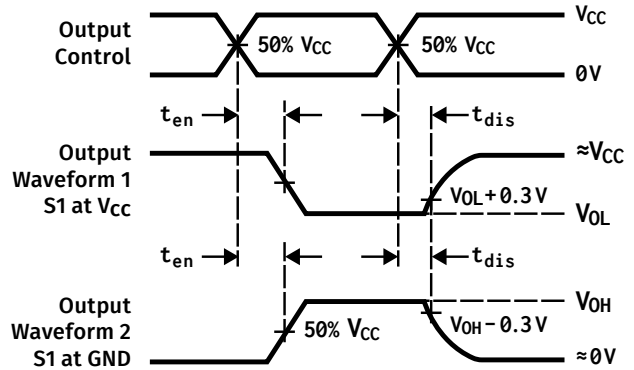


Figure 5: Enable and disable times, for low- and high-level enables

6 DETAILED DESCRIPTION

The AF54RHC245 is a 8-bit 100MHz transceiver with 3-state outputs intended to perform the Boolean function **BUFF** ($Y = A$) in positive logic. Designed to operate from a wide supply voltage of 1.65 to 5.5 V, it has fully redundant input and output stages providing for superior resiliency to single event effects.

The output and input stages are constructed with transient activated clamps (Figure 6, 7) that prevent inadvertent biasing of the V_{CC} power rail through parasitic diodes inherent to conventional input, output, and ESD circuits. The IC also incorporates an internal power-on reset (POR) circuit that prevents the output from driving erroneous results during power-on, and guarantees correct operation at power supply voltages as low as 1.65 V. While the supply is ramping, the POR holds the output buffers in tri-state, a feature that prevents unwanted DC current during cold sparing on input and output pins.

The AF54RHC family's I/O protection circuitry allows for cold sparing configurations as it avoids a leakage current penalty on inputs and outputs while in a power-down state. This can result in considerable power savings in systems where multiple-path redundancy is employed. The ESD clamp circuits for this logic family are designed to support Class 2 ESD levels of 4 kV HBM and 500 V CDM.

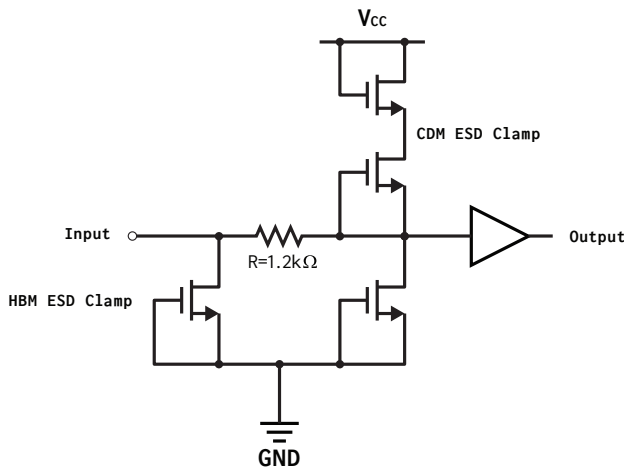


Figure 6: Details of input pin structure

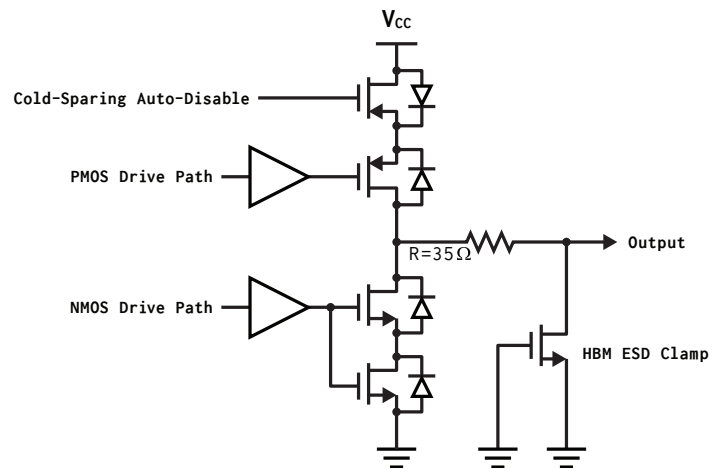


Figure 7: Details of output pin structure

7 APPLICATIONS INFORMATION

7.1 USE IN COLD-SPARING CONFIGURATION

As the AF54RHC family is radiation-hardened by design and includes internal TMR, it can be utilized in high-reliability applications without additional supporting circuitry or devices. Nonetheless, some application requirements call for fully-redundant designs, where an “A” and a “B” device are required, often on separate power rails.

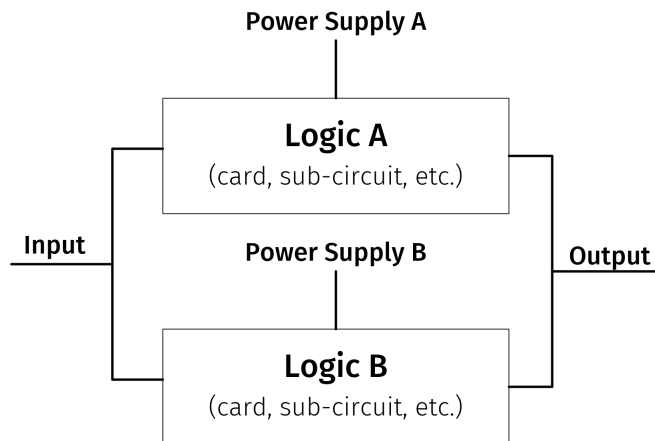


Figure 8: Two-path cold-sparing configuration.

With the cold-sparing capability of the AF54RHC family, fully redundant “A” and “B” functions may be placed in parallel (as seen in Figure 8) running off redundant power supplies. The inputs and outputs on each one of these functions are assumed to be based on the AF54RHC family, allowing for direct parallel connection without unwanted leakage current paths during cold sparing. In the event of a failure in power supply A or within function A, the system can simply shut power supply A off and switch on power supply B, without requiring additional input or output switching or configuration changes.

7.2 POWER SUPPLY RECOMMENDATIONS

This device can operate at any voltage within the range specified in [Table 4 Recommended Operating Conditions](#).

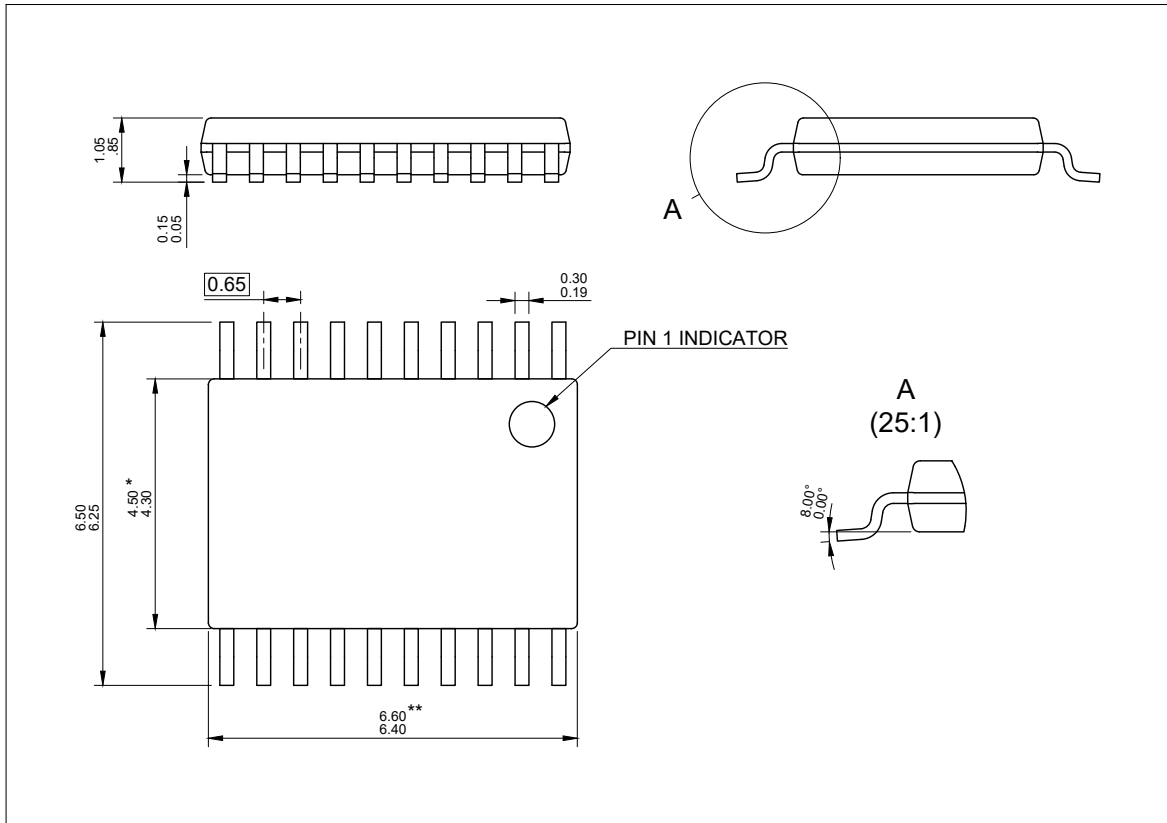
At a minimum, a 16 VDC (or higher), X7R-rated 0.1 μF ceramic decoupling capacitor should be placed near (within 1 cm) the V_{CC} pin of the device.

7.3 APPLICATION TIPS

Unused **inputs** must **not** be left floating. They may be connected to either a low (GND) or high (V_{CC}) bias to provide a known state at the input of the device. Resistors may be used to tie off unused inputs. In the event of a design change, such resistors can be removed, thereby allowing use of the inputs without having to cut traces on the PCB.

An unused **output** may be left floating. It is suggested that it be routed to a test point or similar accessible structure in case the gate needs to be utilized as part of a design revision.

8 PACKAGING INFORMATION



Notes:

1. All linear dimensions are in millimeters. Dimensioning and tolerancing are as per ISO/TS 128-71:2010
2. The part is compliant with JEDEC MO-153 specifications.

* Body width does **not** include interlead flash. Interlead flash shall not exceed 0.25 mm each side.

** Body length does **not** include mold flash, protrusion, or gate burrs. Mold flash, protrusions, and gate burrs shall not exceed 0.15 mm on each side.

Figure 9: Package Mechanical Detail

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9 ORDERING INFORMATION

Example part numbers for the AF54RHC245 are listed in Table 9. The full list of options for this part can be found in Figure 10. Please contact Apogee Semiconductor sales at sales@apogeesemi.com for further information on sampling, lead time and purchasing on specific part numbers.

Table 9: AF54RHC245 Ordering Information

DEVICE	DESCRIPTION	PACKAGE
AF54RHC245ELT-W	Radiation Hardened 8-channel 100MHz Transceiver (for evaluation only)	Plastic TSSOP-20
AF54RHC245ALT-R	Radiation Hardened 8-channel 100MHz Transceiver (300 krad (Si))	Plastic TSSOP-20

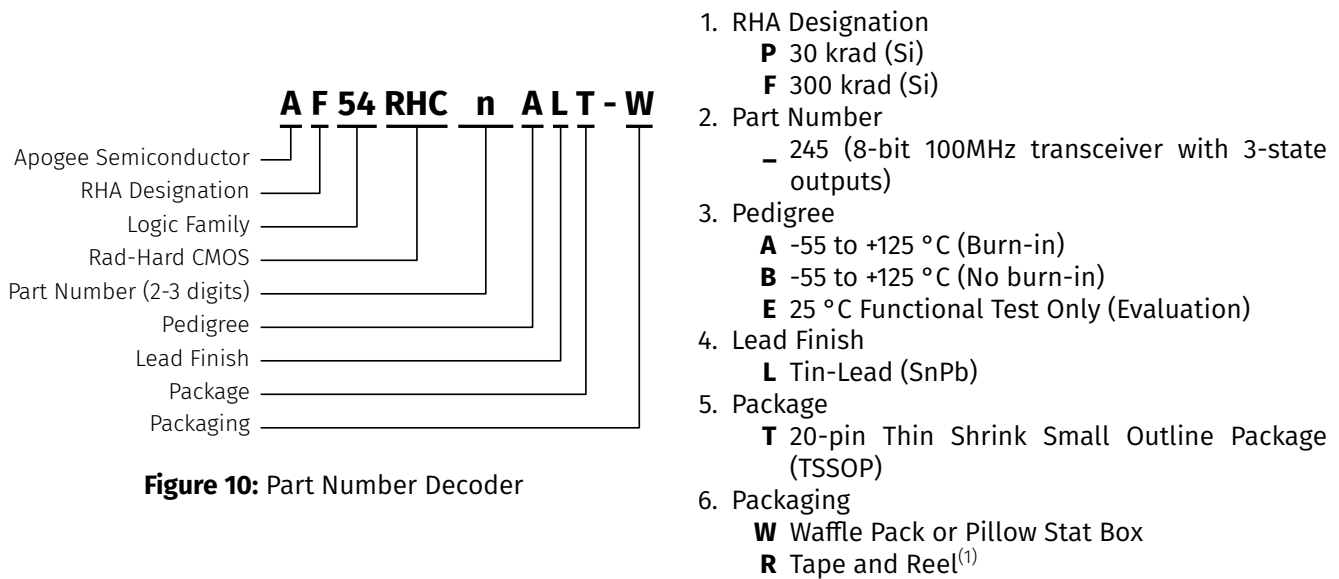


Figure 10: Part Number Decoder

⁽¹⁾ [Contact us](#) for custom reel quantities. Orders less than full reel quantities may be shipped as cut tape.

10 REVISION HISTORY

REVISION	DESCRIPTION	DATE
A00	Initial internal release.	2024-04-29

For the latest version of this document, please visit <https://www.apogeesemi.com>.

11 LEGAL

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